

AMENDMENTS TO THE SPECIFICATION

Approved
K.N. 5/2005
+
O

Please replace paragraph [0018] with the following amended paragraph:

As shown in Fig. 7, a chemical vapor deposition process is performed to form a silicon nitride layer 64 on the inner wall of the deep trench 56, and to fill up the recess 62 with the silicon nitride layer 64 as well. Then a thermal process is performed to diffuse the arsenic ions of the arsenic silicate glass film 58 into the substrate 50, such that a doped region [64] 66 is formed.